High Voltage Power Transistors

DPAK for Surface Mount Applications

Designed for line operated audio output amplifier, switchmode supply drivers and other switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V _{CEO}	250 400	Vdc
Collector–Base Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V _{CB}	350 500	Vdc
Emitter-Base Voltage	V_{EB}	5	Vdc
Collector Current – Continuous	I _C	1	Adc
Collector Current – Peak	I _{CM}	2	Adc
Base Current	I _B	0.6	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.56 0.0125	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

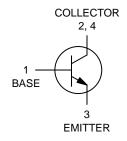
 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



ON Semiconductor®

http://onsemi.com

NPN SILICON POWER TRANSISTORS 1 AMPERE 250, 400 VOLTS, 15 WATTS





DPAK CASE 369C STYLE 1

MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

Jxx = Device Code

xx = 47 or 50

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Case	$R_{ heta JC}$	8.33	°C/W
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{ heta JA}$	80	°C/W
Lead Temperature for Soldering Purpose	TL	260	°C

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	1		1	
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 30 mAdc, I _B = 0) MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V _{CEO(sus)}	250 400	- -	Vdc
Collector Cutoff Current $ \begin{array}{l} (\text{V}_{\text{CE}} = 150 \text{ Vdc, I}_{\text{B}} = 0) \\ \text{MJD47, NJVMJD47T4G} \\ (\text{V}_{\text{CE}} = 300 \text{ Vdc, I}_{\text{B}} = 0) \\ \text{MJD50, NJVMJD50T4G} \end{array} $	I _{CEO}	-	0.2 0.2	mAdc
Collector Cutoff Current	Ices		0.1 0.1	mAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	1	mAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain $(I_C = 0.3 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 1 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$	h _{FE}	30 10	150 -	_
Collector–Emitter Saturation Voltage (I _C = 1 Adc, I _B = 0.2 Adc)	V _{CE(sat)}	-	1	Vdc
Base–Emitter On Voltage (I _C = 1 Adc, V _{CE} = 10 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS	<u> </u>			
Current Gain – Bandwidth Product (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 2 MHz)	f _T	10	-	MHz
Small–Signal Current Gain (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 1 kHz)	h _{fe}	25	-	-
			•	

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

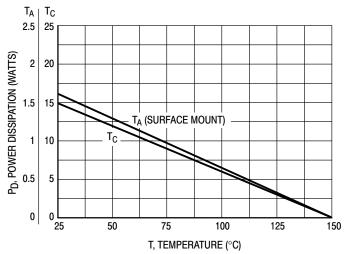


Figure 1. Power Derating

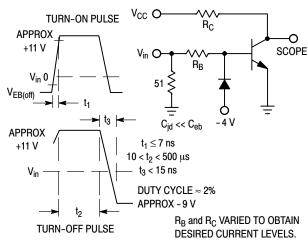


Figure 2. Switching Time Equivalent Circuit

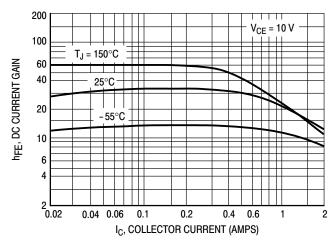


Figure 3. DC Current Gain

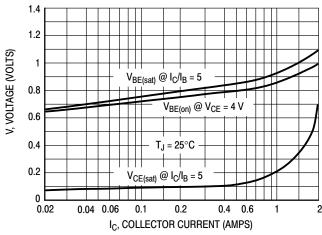


Figure 4. "On" Voltages

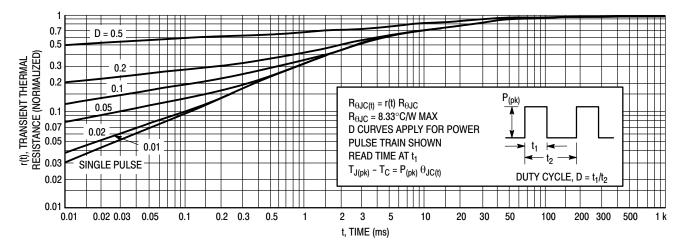


Figure 5. Thermal Response

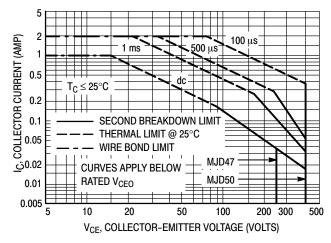


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

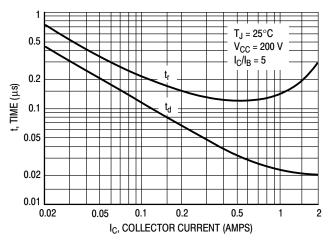


Figure 7. Turn-On Time

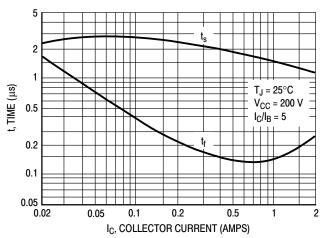


Figure 8. Turn-Off Time

ORDERING INFORMATION

Device	Package	Shipping [†]
MJD47G	369C (Pb-Free)	75 Units / Rail
MJD47T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD47T4G*	369C (Pb-Free)	2,500 / Tape & Reel
MJD50G	369C (Pb-Free)	75 Units / Rail
MJD50T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD50T4G*	369C (Pb-Free)	2,500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specification Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

В

NOTE 7

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TOP VIEW

L3

b2 e

L2 GAUGE

DPAK (SINGLE GAUGE) CASE 369C ISSUE F SCALE 1:1 Α

DETAIL A

C SEATING

C-

SIDE VIEW

DATE 21 JUL 2015

NOTES:

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BOTTOM VIEW

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.086	0.094	2.18	2.38	
A1	0.000	0.005	0.00	0.13	
b	0.025	0.035	0.63	0.89	
b2	0.028	0.045	0.72	1.14	
b3	0.180	0.215	4.57	5.46	
С	0.018	0.024	0.46	0.61	
c2	0.018	0.024	0.46	0.61	
D	0.235	0.245	5.97	6.22	
E	0.250	0.265	6.35	6.73	
е	0.090	BSC	2.29 BSC		
Н	0.370	0.410	9.40	10.41	
L	0.055	0.070	1.40	1.78	
L1	0.114	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC		
L3	0.035	0.050	0.89	1.27	
L4		0.040		1.01	
Z	0.155		3.93		

ALTERNATE CONSTRUCTIONS **DETAIL A** ROTATED 90° CW **GENERIC** STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE PIN 1. GATE 2. DRAIN

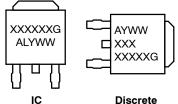
Z

BOTTOM VIEW

С

3. EMITTE 4. COLLE	ER .	3. SOURCE 4. DRAIN	3. AN	ODE THODE	3. GATE 4. ANODE	3.	CATHODE ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE	STYLE 7: PIN 1. GATE 2. COLLE 3. EMITT	PII ECTOR	'LE 8: N 1. N/C 2. CATHODE 3. ANODE		ODE THODE SISTOR ADJUS	2.	0: CATHODE ANODE CATHODE
4. MT2	COLLE	ECTOR	CATHODE	4. CA	THODE	4.	ANODE

MARKING DIAGRAM*



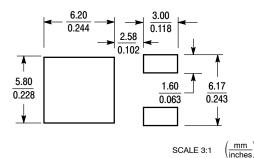
XXXXXX = Device Code = Assembly Location Α L = Wafer Lot Υ = Year WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking.

= Pb-Free Package

G

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

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